

FAST CMOS 16-BIT BUFFER/LINE DRIVER

IDT54/74FCT16244T/AT/CT

FEATURES:

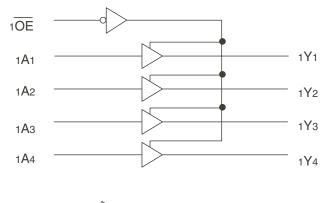
- 0.5 MICRON CMOS Technology
- . High-speed, low-power CMOS replacement for ABT functions
- Typical tsk(o) (Output Skew) < 250ps
- Low input and output leakage ≤ 1µA (max.)
- ESD > 2000V per MIL-STD-883, Method 3015; > 200V using machine model (C = 200pF, R = 0)
- High drive outputs (-32mA IOH, 64mA IOL)
- · Power off disable outputs permit "live insertion"
- Typical Volp (Output Ground Bounce) < 1.0V at Vcc = 5V, TA = 25°C
- Available in the following packages:
 - Industrial: SSOP, TSSOP
 - Military: CERPACK

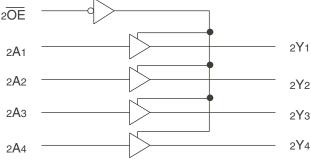
DESCRIPTION:

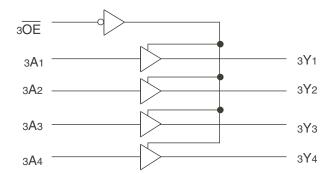
The FCT16244T 16-Bit Buffer/Line Driver is for bus interface or signal buffering applications requiring high speed and low power dissipation. These devices have a flow through pin organization, and shrink packaging to simplify board layout. All inputs are designed with hysteresis for improved noise margin. The three-state controls allow independent 4-bit, 8-bit or combined 16-bit operation. These parts are plug in replacements for 54/74ABT16244 where higher speed, lower noise or lower power dissipation levels are desired.

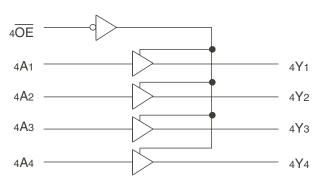
The FCT16244T is ideally suited for driving high capacitance loads (>200pF) and low impedance backplanes. These "high drive" buffers are designed with power off disable capability to allow "live insertion" of boards when used in a backplane interface.

FUNCTIONAL BLOCK DIAGRAM







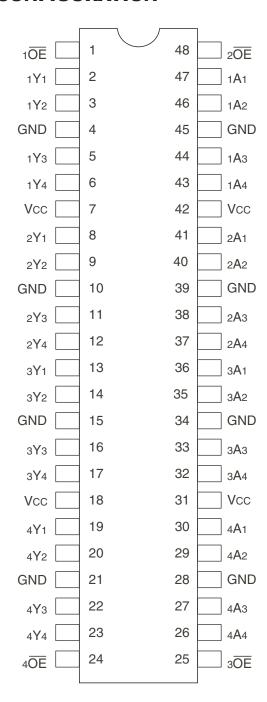


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MILITARY AND INDUSTRIAL TEMPERATURE RANGES

SEPTEMBER 2009

PIN CONFIGURATION



SSOP/ TSSOP/ CERPACK TOP VIEW

ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Description	Max	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7	٧
VTERM ⁽³⁾	Terminal Voltage with Respect to GND	-0.5 to Vcc+0.5	٧
Tstg	Storage Temperature	-65 to +150	°C
lout	DC Output Current	-60 to +120	mA

NOTES:

- 1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. All device terminals except FCT162XXXT Output and I/O terminals.
- 3. Output and I/O terminals terminals for FCT162XXXT and FCT166XXXT.

CAPACITANCE (TA = +25°C, F = 1.0MHz)

	Symbol	Parameter ⁽¹⁾	Conditions	Тур.	Max.	Unit
	CIN	Input Capacitance	VIN = 0V	3.5	6	pF
ſ	Соит	Output Capacitance	Vout = 0V	3.5	8	pF

NOTE:

1. This parameter is measured at characterization but not tested.

PIN DESCRIPTION

Pin Names Description						
xOE 3-State Output Enable Inputs (Active LOW)						
xAx	Data Inputs					
x Y x 3-State Outputs						

FUNCTION TABLE(1)

Inp	Outputs	
х ОЕ	xAx	хҮх
L	L	L
L	Н	Н
Н	Х	Z

NOTE:

1. H = HIGH Voltage Level

X = Don't Care

L = LOW Voltage Level

Z = High-Impedance

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified:

Industrial: TA = -40°C to +85°C, VCC = $5.0V \pm 10\%$; Military: TA = -55°C to +125°C, VCC = $5.0V \pm 10\%$

Symbol	Parameter	Test Condit	ions ⁽¹⁾	Min.	Typ. ⁽²⁾	Max.	Unit
VIH	Input HIGH Level	Guaranteed Logic HIGH Level		2	_	_	V
VIL	Input LOW Level	Guaranteed Logic LOW Level		_	_	0.8	V
lін	Input HIGH Current (Input pins)(5)	Vcc = Max.	VI = VCC	_	_	±1	μA
	Input HIGH Current (I/O pins) ⁽⁵⁾			_	_	±1	
lıL	Input LOW Current (Input pins) ⁽⁵⁾		VI = GND	_	_	±1	
	Input LOW Current (I/O pins) ⁽⁵⁾			_	_	±1	
lozh	High Impedance Output Current	Vcc = Max.	Vcc = Max. Vo = 2.7V		_	±1	μA
lozL	(3-State Output pins) ⁽⁵⁾		Vo = 0.5V	_	_	±1	
Vik	Clamp Diode Voltage	VCC = Min., IN = −18mA	VCC = Min., IIN = -18mA		-0.7	-1.2	V
los	Short Circuit Current	Vcc = Max., Vo = GND ⁽³⁾		-80	-140	-250	mA
VH	Input Hysteresis	-		_	100	_	mV
ICCL ICCH ICCZ	Quiescent Power Supply Current	Vcc = Max. Vin = GND or Vcc		_	5	500	μА

OUTPUT DRIVE CHARACTERISTICS

Symbol	Parameter	Test Co	nditions ⁽¹⁾	Min.	Typ. ⁽²⁾	Max.	Unit
lo	Output Drive Current	$Vcc = Max., Vo = 2.5V^{(3)}$		-50	_	-180	mA
Vон	Output HIGH Voltage	Vcc = Min.	Iон = −3mA,	2.5	3.5	_	V
		VIN = VIH or VIL	IOH = −12mA MIL	2.4	3.5	_	V
			IOH = −15mA IND				
			IOH = -24mA MIL	2	3	_	V
			$IOH = -32mA IND^{(4)}$				
Vol	Output LOW Voltage	Vcc = Min.	IOL = 48mA MIL	_	0.2	0.55	V
		VIN = VIH or VIL	IOL = 64mA IND				
loff	Input/Output Power Off Leakage ⁽⁵⁾	$VCC = 0V$, $VIN \text{ or } VO \le 4.5V$		_	_	±1	μΑ

NOTES:

- 1. For conditions shown as Min. or Max., use appropriate value specified under Electrical Characteristics for the applicable device type.
- 2. Typical values are at Vcc = 5.0V, $+25^{\circ}C$ ambient.
- 3. Not more than one output should be shorted at one time. Duration of the test should not exceed one second.
- 4. Duration of the condition can not exceed one second.
- 5. The test limit for this parameter is $\pm 5\mu A$ at $T_A = -55^{\circ} C$.

POWER SUPPLY CHARACTERISTICS

Symbol	Parameter	Test Condition	ons ⁽¹⁾	Min.	Typ.(2)	Max.	Unit
Δlcc	Quiescent Power Supply Current TTL Inputs HIGH	$VCC = Max.$ $VIN = 3.4V^{(3)}$		_	0.5	1.5	mA
ICCD	Dynamic Power Supply Current ⁽⁴⁾	Vcc = Max. Outputs Open xOE = GND One Input Togging 50% Duty Cycle	Vin = Vcc Vin = GND	1	60	100	μΑ/ MHz
Ic	Total Power Supply Current ⁽⁶⁾	Vcc = Max. Outputs Open fi = 10MHz	VIN = VCC VIN = GND	1	0.6	1.5	mA
		50% Duty Cycle xOE = GND One Bit Toggling	VIN = 3.4V VIN = GND	Ι	0.9	2.3	
		Vcc = Max. Outputs Open fi = 2.5MHz 50% Duty Cycle	VIN = VCC VIN = GND	_	2.4	4.5(5)	
		xOE = GND Sixteen BitsTogging	VIN = 3.4V VIN = GND	_	6.4	16.5 ⁽⁵⁾	

NOTES:

- 1. For conditions shown as Min. or Max., use appropriate value specified under Electrical Characteristics for the applicable device type.
- 2. Typical values are at Vcc = 5.0V, +25°C ambient.
- 3. Per TTL driven input (VIN = 3.4V). All other inputs at Vcc or GND.
- 4. This parameter is not directly testable, but is derived for use in Total Power Supply Calculations.
- 5. Values for these conditions are examples of the lcc formula. These limits are guaranteed but not tested.
- 6. IC = IQUIESCENT + INPUTS + IDYNAMIC

 $IC = ICC + \Delta ICC DHNT + ICCD (fcpNcp/2 + fiNi)$

Icc = Quiescent Current (IccL, IccH and Iccz)

 ΔIcc = Power Supply Current for a TTL High Input (VIN = 3.4V)

DH = Duty Cycle for TTL Inputs High

NT = Number of TTL Inputs at DH

ICCD = Dynamic Current caused by an Input Transition Pair (HLH or LHL)

fcP = Clock Frequency for Register Devices (Zero for Non-Register Devices)

NCP = Number of Clock Inputs at fcP

fi = Input Frequency

Ni = Number of Inputs at fi

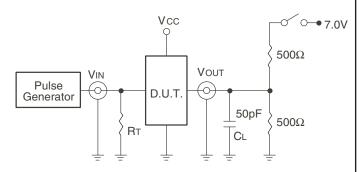
SWITCHING CHARACTERISTICS OVER OPERATING RANGE

			54FCT16244T		54/74FCT16244AT			54/74FCT16224CT					
			M	lil.	Ir	ıd.	Mi	l.	Inc	d.	Mi	l.	
Symbol	Parameter	Condition ⁽¹⁾	Min.(2)	Max.	Min.(2)	Max.	Min.(2)	Max.	Min.(2)	Max.	Min.(2)	Max.	Unit
tPLH	Propagation Delay	CL = 50pF	1.5	7	1.5	4.8	1.5	5.1	1.5	3.4	1.5	4.6	ns
tPHL	xAx to xYx	$RL = 500\Omega$											
tpzh	Output Enable Time		1.5	8.5	1.5	6.2	1.5	6.5	1.5	4.4	1.5	6.5	ns
tPZL													
tPHZ	Output Disable Time		1.5	7.5	1.5	5.6	1.5	5.9	1.5	3.9	1.5	5.7	ns
tPLZ													
tSK(o)	Output Skew ⁽³⁾		_	0.5	_	0.5		0.5		0.5		0.5	ns

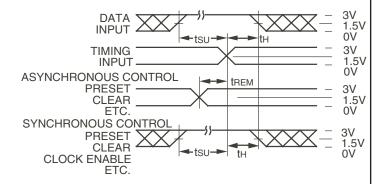
NOTES:

- See test circuit and waveforms.
- 2. Minimum limits are guaranteed but not tested on Propagation Delays.
- 3. Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.

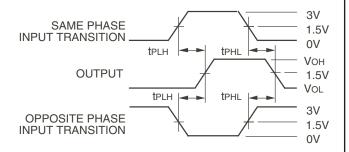
TEST CIRCUITS AND WAVEFORMS



Test Circuits for All Outputs



Set-up, Hold, and Release Times



Propagation Delay

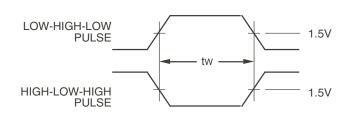
SWITCH POSITION

Test	Switch
Open Drain Disable Low Enable Low	Closed
All Other Tests	Open

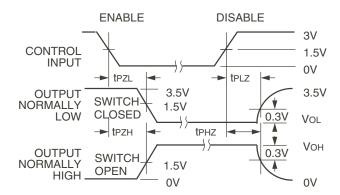
DEFINITIONS:

CL = Load capacitance: includes jig and probe capacitance.

RT = Termination resistance: should be equal to ZouT of the Pulse Generator.



Pulse Width

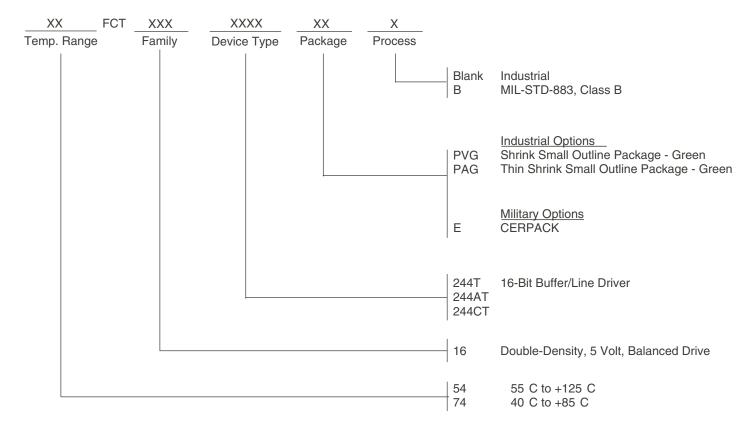


Enable and Disable Times

NOTES:

- 1. Diagram shown for input Control Enable-LOW and input Control Disable-HIGH.
- 2. Pulse Generator for All Pulses: Rate \leq 1.0MHz; tF \leq 2.5ns; tR \leq 2.5ns.

ORDERING INFORMATION



Datasheet Document History

09/06/09 Pg.6 Updated the ordering information by removing the "IDT" notation and non RoHS part.

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(Rev.1.0 Mar 2020)

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TOYOSU FORESIA, 3-2-24 Toyosu, Koto-ku, Tokyo 135-0061, Japan www.renesas.com

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